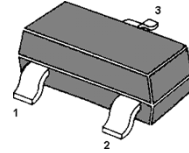


MMBT5400 PNP Silicon Epitaxial Planar Transistor

for high voltage .

Marking Code:2L



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	130	V
Collector Emitter Voltage	$-V_{CEO}$	120	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current Continuous	$-I_C$	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_S	-55 to +150	$^\circ\text{C}$

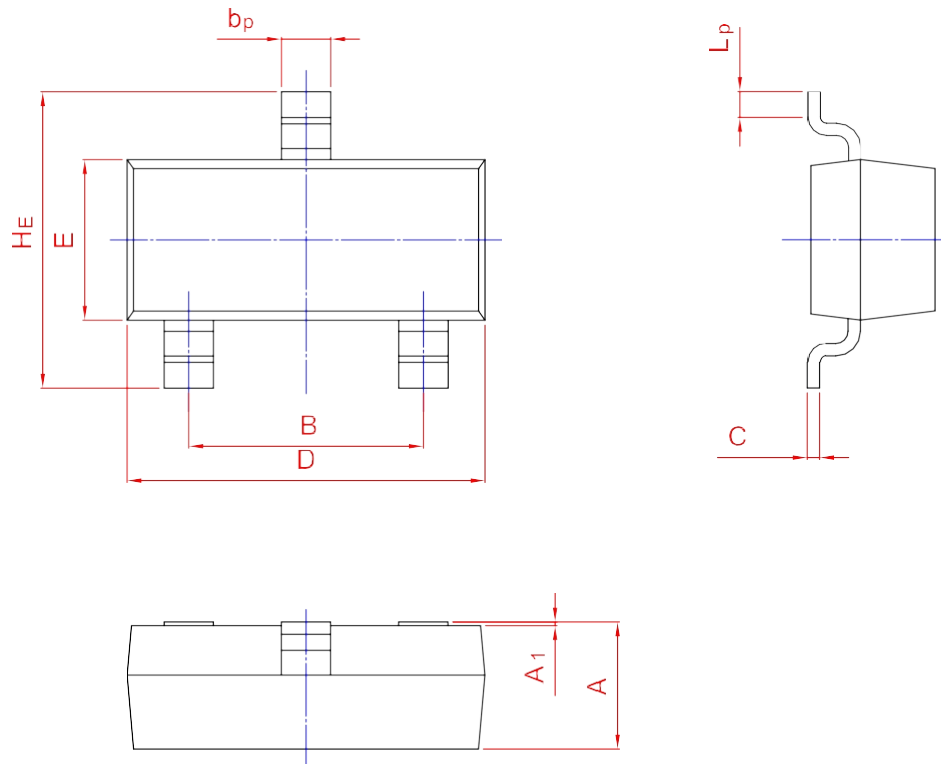
Characteristics at $T_{amb}=25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}=5\text{V}$, $-I_C=10\text{mA}$	h_{FE}	40	180	-
Collector Base Breakdown Voltage at $-I_C=0.1\text{mA}$	$-V_{(BR)CBO}$	130	-	V
Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	120	-	V
Emitter Base Breakdown Voltage at $-I_E=0.1\text{mA}$	$-V_{(BR)EBO}$	5	-	V
Collector Cutoff Current at $-V_{CB}=100\text{V}$	$-I_{CBO}$	-	0.05	μA
Emitter Cutoff Current at $-V_{EB}=3\text{V}$	$-I_{EBO}$	-	0.05	μA
Collector Emitter Saturation Voltage at $-I_C=50\text{mA}$, $-I_B=5\text{mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C=50\text{mA}$, $-I_B=5\text{mA}$	$-V_{BE(sat)}$	-	1	V
Current Gain Bandwidth Product at $-V_{CE}=10\text{V}$, $-I_C=10\text{mA}$	f_T	100	-	MHz
Output Capacitance at $-V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{ob}	-	6	pF
Noise Figure at $-I_C=0.2\text{mA}$, $-V_{CE}=5\text{V}$, $f=15.7\text{KHz}$	NF	-	8	dB

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20